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	Number	Hits	Search Text	DB	Time stamp
2		15940	430/5,311,313,314,316,317.ccls.	USPAT;	2004/02/24 11:14
			438/296,424,427,692,697.ccls.	US-PGPUB;	
			,	EPO; JPO;	
				DERWENT;	
				IBM_TDB	
3		121075	silicon adj nitride "si.sub.3 n.sub.4"	USPAT;	2004/02/24 11:15
			si3n4 sixny "si.sub.x n.sub.y"	US-PGPUB;	
				EPO; JPO;	
				DERWENT	
4		272236	oxide near (region layer coating material	USPAT;	2004/02/24 11:15
-1		272230	film)	US-PGPUB;	2001, 02, 21 11:13
			LIIM,	EPO; JPO;	
	-			DERWENT	
_		44673			2004/02/24 11:16
5		44673	planariz\$5 planaris\$5	USPAT;	2004/02/24 11:16
			•	US-PGPUB;	
				EPO; JPO;	
				DERWENT	
6		43406	cmp (((chemical\$3 adj mechanical\$3)	USPAT;	2004/02/24 11:16
			(chemical\$3-mechanical\$3)) adj polish\$3)	US-PGPUB;	
			chemical\$3-mechanical\$3-polish\$3	EPO; JPO;	
				DERWENT	
8		46117	active near region	USPAT;	2004/02/24 11:17
J			accurate region	US-PGPUB;	
				EPO; JPO;	
_		45.0		DERWENT	0004/00/04 11 17
1		456		USPAT;	2004/02/24 11:17
			WU-J-Yin. LUR-WATERin. LUR-Win.	US-PGPUB;	
				EPO; JPO;	
				DERWENT;	
			·	IBM TDB	
9		12559	sti! (shallow adj trench adj isolation)	USPAT;	2004/02/24 11:19
-				US-PGPUB;	
				EPO; JPO;	
			DERWENT		
10		1318	(420/5 211 212 214 216 217 cclc	USPAT;	2004/02/24 11:35
ΤO		1318	(430/5,311,313,314,316,317.ccls.		2004/02/24 11:35
			438/296,424,427,692,697.ccls.) and (sti!	US-PGPUB;	
			(shallow adj trench adj isolation))	EPO; JPO;	•
		,		DERWENT	
11		701	(active near region) near2 small\$2	USPAT;	2004/02/24 12:08
				US-PGPUB;	
		·		EPO; JPO;	
				DERWENT	
12		712	(active near region) near2 larg\$2	USPAT;	2004/02/24 12:08
			(US-PGPUB;	
				EPO; JPO;	-
			·		
1 ^		7750	thurs a de a h	DERWENT	2004/02/24 11 25
13		77533	trench	USPAT;	2004/02/24 11:36
				US-PGPUB;	
				EPO; JPO;	
				DERWENT	
7		23	partial adj reverse adj2 (mask active	USPAT;	2004/02/24 11:42
			photoresist)	US-PGPUB;	
			*	EPO; JPO;	
	.		DERWENT		
16		75	(reverse near2 (mask active photoresist))	USPAT;	2004/02/24 11:45
тΩ		/3			2004/02/24 11:45
			same (sti! (shallow adj trench adj	US-PGPUB;	
	isolation))	EPO; JPO;			
				DERWENT	
		58	((reverse near2 (mask active photoresist))	USPAT;	2004/02/24 11:45
17			same (sti! (shallow adj trench adj	US-PGPUB;	
17			isolation))) not (partial adj reverse adj2	EPO; JPO;	
17			(mask active photoresist))	DERWENT	
17					1
		. 446	•	USPAT:	1 2004/02/24 12:08
17 18		446	' · · · · · · · · · · · · · · · · · ·	USPAT;	2004/02/24 12:08
		446	•	US-PGPUB;	2004/02/24 12:08
		446	•	US-PGPUB; EPO; JPO;	2004/02/24 12:08
18			(active near region) near2 narrow\$2	US-PGPUB; EPO; JPO; DERWENT	
		1364	•	US-PGPUB; EPO; JPO; DERWENT USPAT;	2004/02/24 12:08
18			(active near region) near2 narrow\$2	US-PGPUB; EPO; JPO; DERWENT USPAT; US-PGPUB;	
18			(active near region) near2 narrow\$2	US-PGPUB; EPO; JPO; DERWENT USPAT;	

21	10	(silicon adj nitride "si.sub.3 n.sub.4" si3n4 sixny "si.sub.x n.sub.y") same (oxide near (region layer coating material film)) same ((planariz\$5 planaris\$5) (cmp (((chemical\$3 adj mechanical\$3) (chemical\$3-mechanical\$3)) adj polish\$3) chemical\$3-mechanical\$3-polish\$3)) same trench same (((active near region) near2 small\$2) ((active near region) near2	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/02/24 12:	20
22	8	narrow\$2)) same (((active near region) near2 larg\$2) ((active near region) near2 wid\$2))	USPAT;	2004/02/24 12:	23
		or ("20030129808")).PN.	US-PGPUB; EPO; JPO; DERWENT	2001, 02, 21 12.	
23	2	("6486040").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/02/24 12:	45
25	8	(("5792707") or ("5837612") or ("5854133") or ("5858842")).PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/02/24 13:	00
26	2	("6004863").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/02/24 13:	19